Product Specification

QND50P02BY

20V P-Channel MOSFET

FEATURES

- -20V, -55A

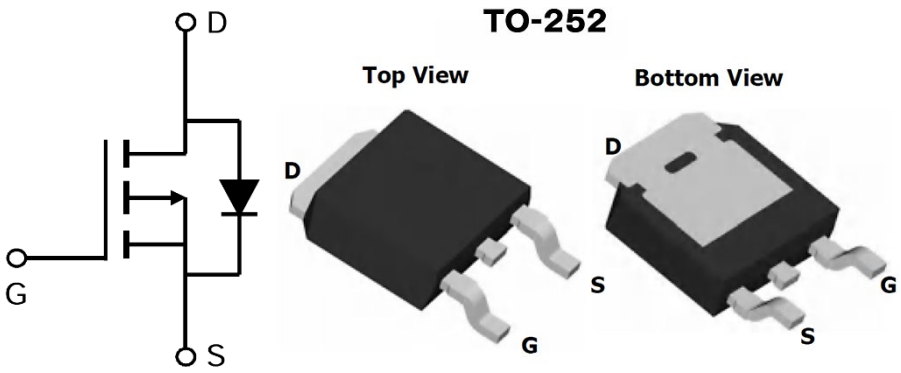
  $R_{DS(ON)}$ Typ = 6.2mΩ @ V_{GS} = -4.5V

  $R_{DS(ON)}$ Typ = 8.4mΩ @ V_{GS} = -2.5V
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge

Applications

- Load Switch
- PWM Application
- Power Management

Pin Description



NO.	Symbol	Description
1	G	GATE
2	D	DRAIN
3	S	SOURCE

Absolute Maximum Ratings

(@ T_C = 25℃ unless otherwise specified)

Symbol	Parameter		Value	Units
V_{DS}	Drain-to-Source Voltage		-20	V
V_{GS}	Gate-to-Source Voltage		±12	V
I_D	Continuous Drain Current	T_A = 25℃	-55	A
		T_A = 100℃	-33	
I_{DM}	Pulsed Drain Current (1)		-220	A
EAS	Single Pulsed Avalanche Energy (2)		39	mJ
P_D	Power Dissipation	T_A = 25℃	41.6	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		3	℃/W
T_J, T_{STG}	Junction & Storage Temperature Range		-55 to 150	℃

Electrical Characteristics

(T_J = 25℃ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Off Characteristics						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	I_D=-250 μA, V_{GS}=0V	-20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-20V, V_{GS}=0V	-	-	-1.0	μA
I_{GSS}	Gate-Body Leakage Current	V_{DS}=0V, V_{GS}=±12V	-	-	±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250μA	-0.4	-0.65	-1	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance(3)	V_{GS}=-4.5V, I_D=-15 A	-	6.2	8.1	mΩ
		V_{GS}=-2.5V, I_D=-10A	-	8.4	11	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=-10V, f=1MHz	-	2888	-	pF
C_{oss}	Output Capacitance		-	380	-	pF
C_{rss}	Reverse Transfer Capacitance		-	342	-	pF
Q_g	Total Gate Charge	V_{GS}=0~-4.5V V_{DS}=-10V, I_D=-15A	-	54	-	nC
Q_{gs}	Gate Source Charge		-	7	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	14	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-On DelayTime	VGS=-10V, VDD =-10V I_D= -13A, R_{GEN}=3	-	13	-	ns
t_r	Turn-On Rise Time		-	105	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	145	-	ns
t_f	Turn-Off Fall Time		-	150	-	ns
Drain-Source Diode Characteristics and Max Ratings						
I_S	Maximum Continuous Drain to Source Diode		-	-	-55	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward		-	-	-220	A
V_{SD}	Drain to Source Diode	V_{GS}=0V, I_S=-15A	-	-	-1.2	V
trr	Body Diode Reverse Recovery	I_F=-15A, di/dt=100A/us	-	26	-	ns
Qrr	Body Diode Reverse Recovery		-	15	-	nC

Notes:

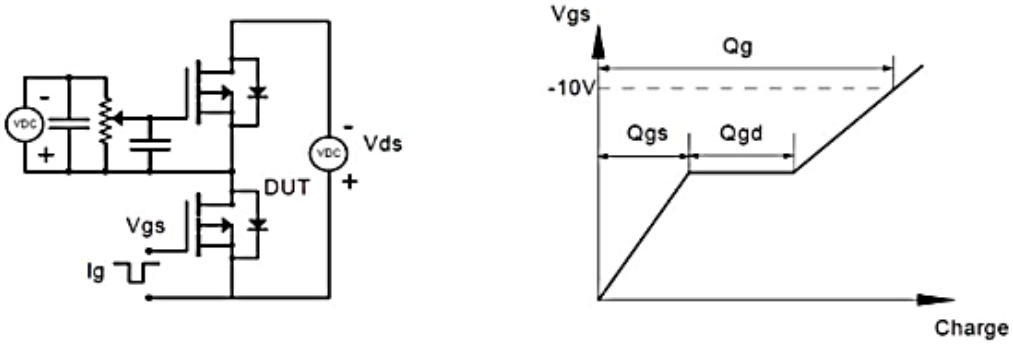
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: T_J=25℃,V_{DD}=-10V,V_G=-10V, R_G=25Ω, L=0.5mH,I_{AS}=-12.5A

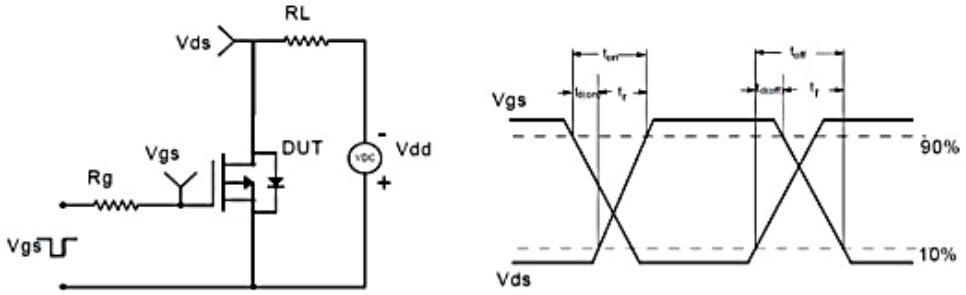
3. Pulse Test: Pulse Width≤300us, Duty Cycle≤0.5%

Test Circuit

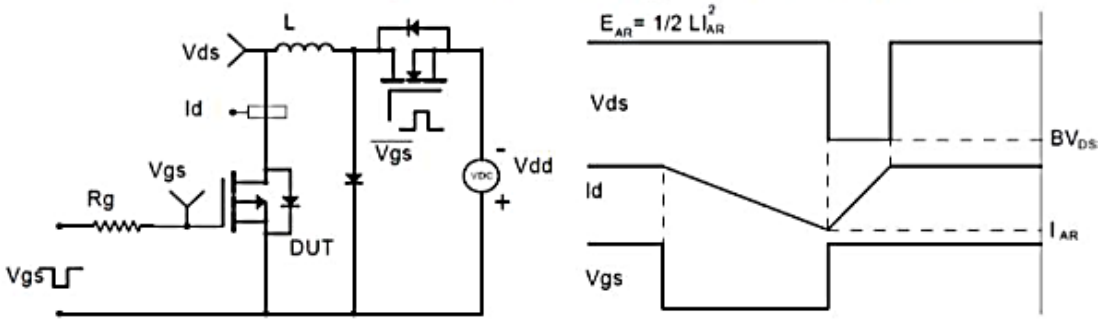
Gate Charge Test Circuit & Waveform



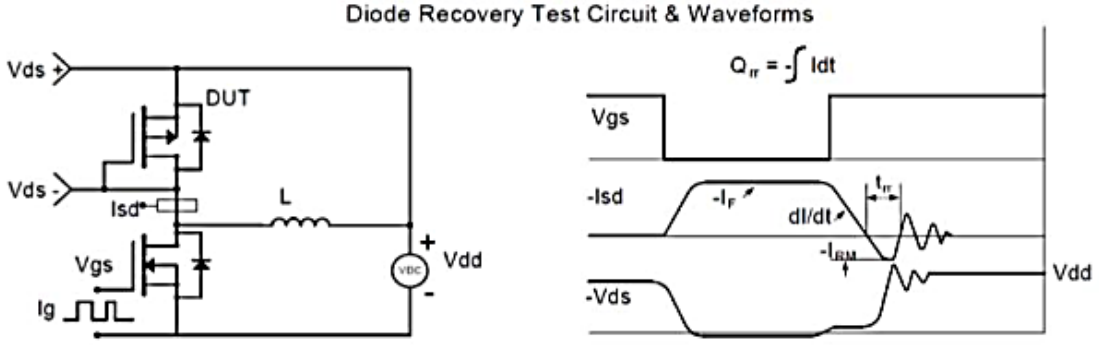
Resistive Switching Test Circuit & Waveforms



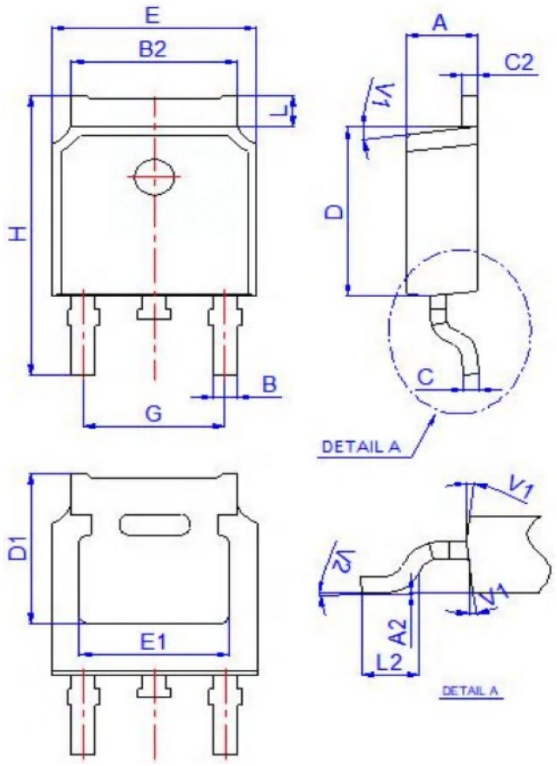
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Mechanical Data(TO-252-3L)



Ref.	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.10	2.50	0.083	0.098
A2	0	0.10	0	0.004
B	0.66	0.86	0.026	0.034
B2	5.18	5.48	0.202	0.216
C	0.40	0.60	0.016	0.024
C2	0.44	0.58	0.017	0.023
D	5.90	6.30	0.232	0.248
D1	5.30 REF		0.209 REF	
E	6.40	6.80	0.252	0.268
E1	4.63		0.182	
G	4.47	4.67	0.176	0.184
H	9.50	10.70	0.374	0.421
L	1.09	1.21	0.043	0.048
L2	1.35	1.65	0.053	0.065
V1	7°		7°	
V2	0°	6°	0°	6°

Ordering information

Order Code	Package	V_{DS}(V)	I_D(A)	$R_{DS(ON)}$(mΩ)	
QND50P02BY	TO-252	-20	-55	V_{GS}=-4.5V	6.2
				V_{GS}=-2.5V	8.4